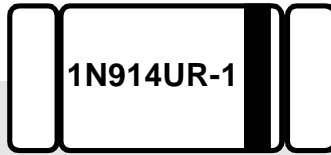


# MINI-MELF-SMD



# Silicon Switching Diode

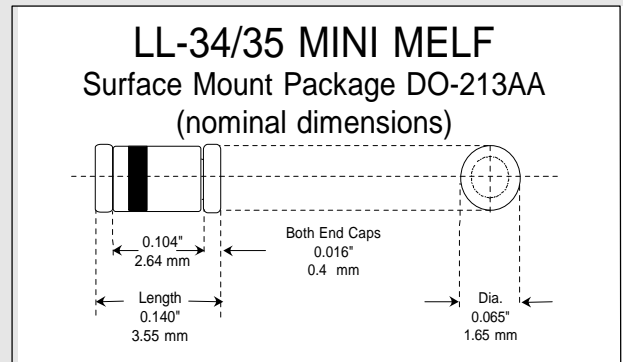
## Applications

Used in general purpose applications, where performance, space and switching speed are important.

## Features

- Six sigma quality
- Metallurgically bonded
- BKC's Sigma Bond™ plating for problem free solderability
- Also comes in DO-35 glass package
- Full UR approval to Mil-S-19500/116
- Available up to JANTXV levels
- "S" level screening available to Source Control Drawings

## 1N914UR-1 / LL914



Maximum Ratings	Symbol	Value	Unit
Peak Inverse Voltage	PIV	100 (Min.)	Volts
Average Rectified Current	$I_{Avg}$	200	mAmps
Continuous Forward Current	$I_{Fdc}$	300	mAmps
Peak Surge Current ( $t_{peak} = 1 \text{ sec.}$ )	$I_{peak}$	1.0	Amp
BKC Power Dissipation @ end cap $T = 50 \text{ }^\circ\text{C}$	$P_{tot}$	500	mWatts
Storage & Operating Temperature Range	$T_{St \& Op}$	-65 to +200	$^\circ\text{C}$

Electrical Characteristics @ 25°C	Symbol	Maximum Limits	Unit
Forward Voltage Drop @ $I_F = 10 \text{ mA}$	$V_F$	1.0	Volts
Forward Voltage Drop @ $I_F = 100 \text{ mA}$	$V_F$	1.2	Volts
Reverse Leakage Current @ $V_R = 20 \text{ V}$	$I_R$	0.025 (50 @ 150 °C)	$\mu\text{A}$
Reverse Leakage Current @ $V_R = 75 \text{ V}$	$I_R$	0.50 (100 @ 150 °C)	$\mu\text{A}$
Capacitance @ $V_R = 0 \text{ V}$ , $f = 1 \text{ MHz}$	$C_T$	4.0	pF
Capacitance @ $V_R = 1.5 \text{ V}$ , $f = 1 \text{ MHz}$	$C_T$	2.8	pF
Reverse Recovery Time (note 1)	$t_{rr}$	5.0	nSecs
Forward Recovery Time (note 2)	$V_{fr}$	20	nSecs

Note 1:  $I_F = I_R = 10 \text{ mA}$ ,  $R_L = 100 \text{ Ohms}$  Note 2:  $I_F = 50 \text{ mA dc}$

To order MIL parts, use the 1N914UR-1 number with the appropriate JAN, JTX or JTXV prefix.

1N914-1 DO-35 glass leaded parts also available in both commercial and military versions.